NSN 5961-00-415-8419

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View Online at https://aerobasegroup.com/nsn/5961-00-415-8419 **Inclosure Material:** Metal **Overall Length:** Between 0.330 inches and 0.505 inches Overall Diameter: 0.650 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** Between 0.544 inches and 0.562 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 breakover voltage, dc **Current Rating Per Characteristic:** 7.50 amperes source cutoff current **Power Rating Per Characteristic:** 2.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 120.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pnp **Thread Series Designator: Terminal Type And Quantity:** 1 threaded stud and 2 tab, solder lug **Specification Data:** 80131-release5040 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:**

Demilitarization: No

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